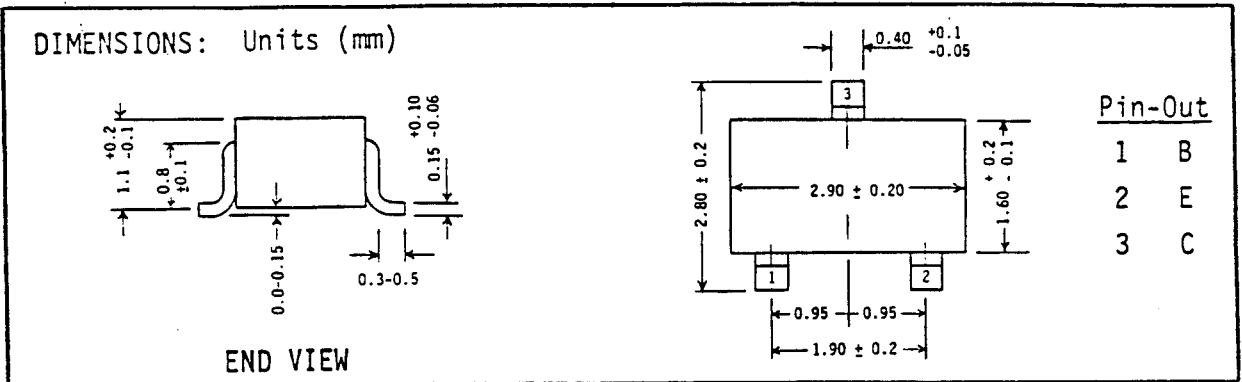


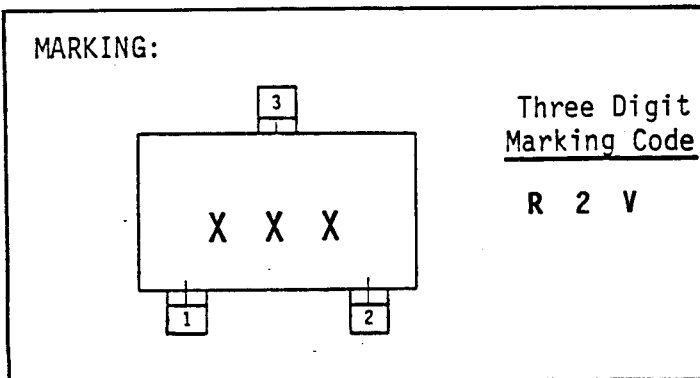
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SUBJECT		
SOT-23 TRANSISTOR, PNP, SILICON		

ABSOLUTE MAXIMUM RATINGS: (Ta = 25°C)

Collector-Base Voltage	V _{CB0}	30 V
Collector-Emitter Voltage	V _{CE0}	30 V
Emitter-Base Voltage	V _{EB0}	10 V
Collector Current	I _C	500 mA
Power Dissipation-Free Air	P _D	200 mW
Power Dissipation-Ceramic Substrate	P _D	350 mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-55 to 150 °C
Solder Temperature (10 seconds)		260 °C



THE JAPANESE STYLE SC-59 PACKAGE



PACKAGING:

—	BULK, 500 per BAG
—	MAGAZINES OF 50 EACH
—	8mm T&R, T-146 3K/REEL
—	8mm T&R, T-147 3K/REEL
—	8mm T&R, T-24610K/REEL
—	8mm T&R, T-24710K/REEL

REMARKS: PROCESS: B-25 Thermal Resistance R_{θJA} 625 °C/Watt
FREE AIR, T_A = 25°C

ROHM ELECTRONICS
3034 Owen Drive, Antioch, TN 37013
TEL: (615) 641-2020 FAX: (615) 641-2022

APPROVAL

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DESIGN

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MASTER

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TRANSISTOR, PNP ,SILICON SOT-23

ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unless Otherwise Specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV _{CES}	I _C = 100 uA	30			V
I _{CB0}	V _{CB} = 30 V		1.0	100	nA
I _{EB0}	V _{EB} = 10 V		1.0	100	nA
h _{FE}	I _C = 10 mA, V _{CE} = 5 V	10,000			
h _{FE}	I _C = 100 mA, V _{CE} = 5 V	20,000			
V _{CE(SAT)}	I _C = 100 mA, I _B = 100 uA			1.5	V
V _{BE(ON)}	I _C = 100 mA, V _{CE} = 5 V			2.0	V
f _T	I _C = 100 mA, V _{CE} = 5 V, f = 100MHz	125			MHz
C _{ob}	V _{CB} = 10 V, I _E = 0, f = 100KHz		4.0		pF
h _{fe}	I _C = 10 mA, V _{CE} = 5 V, f = 1.0KHz		35,000		
NF	I _C = 1.0 mA, V _{CE} = 5 V, R _s = 100KΩ f = 1.0 KHz		2.0		dB

R-Ohm Corporation P.O. Box 19515 Irvine, California 92713	APPROVAL <i>[Signature]</i> 10/12/89	CHECK ✓	DESIGN
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MASTER